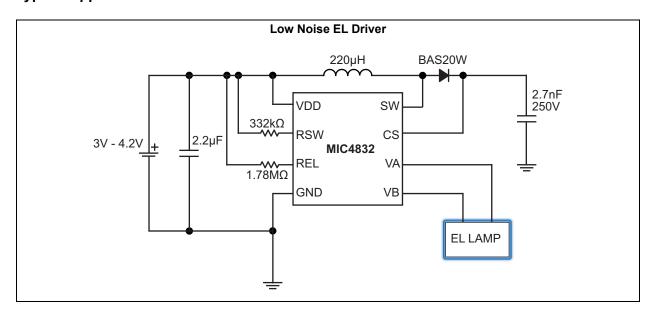
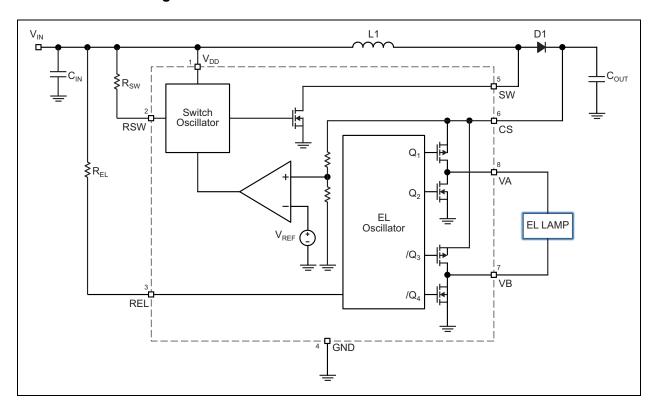
# **Typical Application Circuit**



# **Functional Block Diagram**



#### 1.0 ELECTRICAL CHARACTERISTICS

#### **Absolute Maximum Ratings †**

Supply Voltage (V <sub>DD</sub> )	
Output Voltage (V <sub>CS</sub> )	
EL Lamp Terminals (V <sub>A</sub> , V <sub>B</sub> )	
Switch Voltage (V <sub>SW</sub> )	
Frequency Control Voltage (V <sub>RSW</sub> , V <sub>RFL</sub> )	
ESD Rating (Note 1)	

### **Operating Ratings ††**

† Notice: Exceeding the absolute maximum ratings may damage the device.

**†† Notice:** The device is not guaranteed to function outside its operating ratings.

Note 1: Devices are ESD sensitive. Handling precautions recommended. Human body model, 1.5 k $\Omega$  in series with 100 pF.

### **ELECTRICAL CHARACTERISTICS**

**Electrical Characteristics:**  $V_{IN} = V_{DD} = 3.0V$ ,  $R_{SW} = 338$  kΩ,  $R_{EL} = 1.78$  MΩ.  $T_A = +25$ °C unless otherwise specified. **Bold** values valid for -40°C  $\leq T_A \leq +85$ °C. Note 1

specified. <b>Bold</b> values valid for –40°C ≤ 1 <sub>A</sub> ≤ +85°C. Note 1									
Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions			
On-Resistance	R <sub>DS(ON)</sub>		3.8	7	Ω	I <sub>SW</sub> = 100 mA			
CS Voltage Variation	$V_{CS}$	91	105	119	٧	_			
Enable Input Low Voltage (Turn-Off)	V <sub>EN-L</sub>	ı	ı	0.5	>	V <sub>DD</sub> = 1.8V to 5.5V			
Enable Input High Voltage (Turn-On)	V <sub>EN-H</sub>	V <sub>DD</sub> – 0.5	ı	ı	٧	V <sub>DD</sub> = 1.8V to 5.5V			
Shutdown Current	I <sub>SD</sub>	1	0.01	0.5	μΑ	R <sub>SW</sub> Resistor = Low; R <sub>EL</sub> Resistor = Low; V <sub>DD</sub> = 5.5V			
Input Supply Current	I <sub>VDD</sub>	ı	45	75	μΑ	R <sub>SW</sub> Resistor = High; R <sub>EL</sub> Resistor = High; V <sub>CS</sub> = 110V; V <sub>A</sub> , V <sub>B</sub> = OPEN			
Input Current Including Inductor	I <sub>CS</sub>		24		mA	$V_{IN} = V_{DD} = 3.2V; R_{SW} = 338 kΩ,$ $R_{EL} = 1.78 MΩ;$ $L = 220 \mu H; R_{OUT} = 10 kΩ; Lamp = 2 in2$			
V <sub>A</sub> – V <sub>B</sub> Output Drive Frequency	f <sub>EL</sub>	158	200	242	Hz	R <sub>EL</sub> = 1.78 MΩ			
Switching Transistor Frequency	f <sub>SW</sub>	90	112	134	kHz	R <sub>SW</sub> = 338 kΩ			
Switching Transistor Duty Cycle	D		90		%	_			

Note 1: Specification for packaged product only.

## **TEMPERATURE SPECIFICATIONS**

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions	
Temperature Ranges							
Storage Temperature Range	T <sub>S</sub>	-65	_	+150	°C	_	
Ambient Temperature Range	T <sub>A</sub>	-40	_	+85	°C	_	
Package Thermal Resistance							
Thermal Resistance 8-Lead DFN	$\theta_{JA}$	_	63	_	°C/W	_	
Thermal Resistance MSOP-8	$\theta_{JA}$	_	206	_	°C/W	_	

Note 1: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e.,  $T_A$ ,  $T_J$ ,  $\theta_{JA}$ ). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +125°C rating. Sustained junction temperatures above +125°C can impact the device reliability.

#### 2.0 TYPICAL PERFORMANCE CURVES

The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

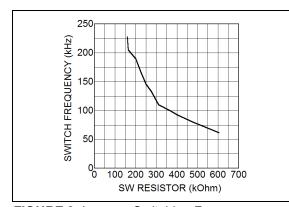


FIGURE 2-1: SW Resistor.

Note:

Switching Frequency vs.

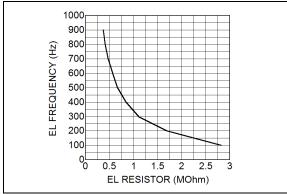


FIGURE 2-2: Resistor.

EL Frequency vs. EL

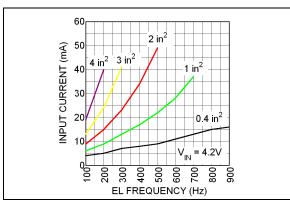


FIGURE 2-3: Frequency.

Input Current vs. EL

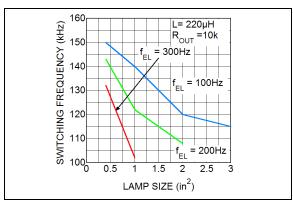


FIGURE 2-4: Lamp Size.

Switching Frequency vs.

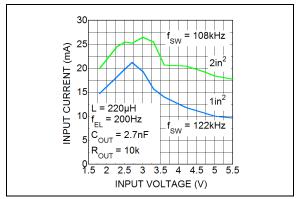


FIGURE 2-5: Voltage.

Total Input Current vs. Input

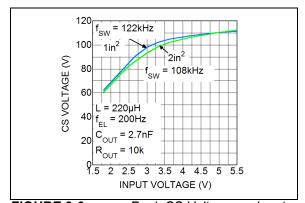
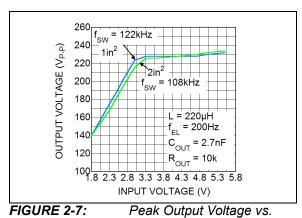


FIGURE 2-6:

Peak CS Voltage vs. Input

Voltage.



Input Voltage.

# 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	VDD	Supply (Input): 1.8V to 5.5V for internal circuitry.
2	RSW	Switch Resistor (External Component): Set switch frequency of the internal power MOSFET by connecting an external resistor to VDD. Connecting the external resistor to GND disables the switch oscillator and shuts down the device.
3	REL	EL Resistor (External Component): Set EL frequency of the internal H-Bridge driver by connecting an external resistor to VDD. Connecting the external resistor to GND disables the EL oscillator.
4	GND	Ground.
5	SW	Switch Node (Input): Internal high-voltage power MOSFET drain.
6	CS	Regulated Boost Output (External Component): Connect to the output capacitor of the boost regulator and connect to the cathode of the diode.
7	VB	EL Output: Connect to one end of the EL lamp. Polarity is not important.
8	VA	EL Output: Connect to one end of the EL lamp. Polarity is not important.

## 4.0 FUNCTIONAL DESCRIPTION

#### 4.1 Overview

The MIC4832 is a high-voltage EL driver with an AC output voltage of 220V peak-to-peak that's capable of driving EL lamps up to 3 in². Input supply current for the MIC4832 is typically 45  $\mu A$ , reducing to 10 nA in shutdown. The high voltage EL driver has two internal oscillators to control the switching MOSFET and the H-Bridge driver. Both of the internal oscillators' frequencies can be individually programmed through the external resistors to maximize the efficiency and the brightness of the EL lamp.

## 4.2 Regulation

Referring to the Functional Block Diagram, initially power is applied to V<sub>DD</sub>. The internal feedback voltage is less than the reference voltage, causing the internal comparator to go high, which then enables the switching MOSFET's oscillator. When the switching MOSFET turns on, current flows through the inductor and flows into the switch. The switching MOSFET will typically turn on for 90% of the switching period. During the on-time, energy is stored in the inductor. When the switching MOSFET turns off, current flowing into the inductor forces the voltage across the inductor to reverse polarity. The voltage across the inductor rises until the external diode conducts and clamps the voltage at  $V_{OUT} + V_{D1}$ . The energy in the inductor is then discharged into the C<sub>OUT</sub> capacitor. The internal comparator continues to turn the switching MOSFET on and off until the internal feedback voltage is above the reference voltage. Once the internal feedback voltage is above the reference voltage, the internal comparator turns off the switching MOSFET's oscillator.

When the EL oscillator is enabled,  $V_A$  and  $V_B$  switch in opposite states to achieve a 220V peak-to-peak AC output signal. The external resistor that connects to the REL pin determines the EL frequency.

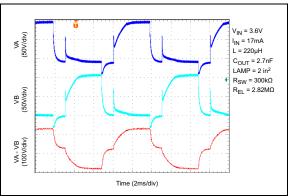


FIGURE 4-1: 100 Hz Output Waveform

#### 4.3 Switching Frequency

The switching frequency of the converter is controlled via an external resistor between the RSW pin and VDD pin of the device. The switching frequency increases as the resistor value decreases. For resistor value selections, see Figure 2-1 or use Equation 4-1. The switching frequency range is 65 kHz to 250 kHz, with an accuracy of ±20%. In general, the lower the switching frequency, the greater the input current is drawn to deliver more power to the output. However, the switching frequency should not be so low as to allow the voltage at the switch node or the CS pin to go beyond the absolute maximum voltage of those pins.

#### **EQUATION 4-1:**

$$f_{SW}\langle kHz\rangle = \frac{36}{R_{SW}(M\Omega)}$$

#### 4.4 EL Frequency

The EL lamp frequency is controlled via an external resistor connected between the REL pin and VDD pin of the device. The lamp frequency increases as the resistor value decreases. For resistor value selections, see Figure 2-2 or use Equation 4-2. The EL lamp frequency range is 60 Hz to 1000 Hz, with an accuracy of ±20%.

#### **EQUATION 4-2:**

$$f_{EL}(Hz) = \frac{360}{R_{EL}(M\Omega)}$$

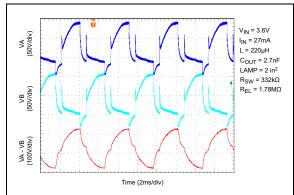


FIGURE 4-2: 200 Hz Output Waveform.

In general, as the EL lamp frequency increases, the amount of current drawn from the battery will increase. The color of the EL lamp and the intensity are dependent upon its frequency.

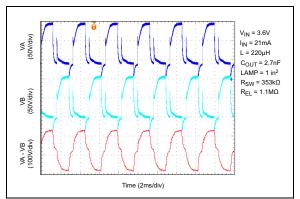


FIGURE 4-3: 300 Hz Output Waveform.

### 4.5 Enable Function

The MIC4832 is disabled by connecting the external resistor ( $R_{SW}$ ) to GND. This turns off the switch oscillator of the boost converter. Connecting the external resistor ( $R_{SW}$ ) to VDD enables the oscillator and turns on the device. The enable voltage should rise or fall monotonically without interruption.

#### 5.0 APPLICATION INFORMATION

#### 5.1 Inductor

A 220  $\mu$ H Murata (LQH4C221K04) inductor is recommended for most applications. Generally, inductors with smaller values can handle more current. Lowering the inductance allows the boost regulator to draw more input current to deliver more energy every cycle. As a result, a lower value inductor may be used to drive larger panels or make the current panel brighter. However, caution is required as using a low value inductor with a low switching frequency may result in voltages exceeding the absolute maximum rating of the switch node and/or the CS pin. If the application uses a low input voltage (1.8V to 3V), a lower value inductor, such as 100  $\mu$ H, may be used in order to drive the EL lamp at max brightness without issue.

#### 5.2 Diode

The diode must have a high reverse voltage (150V), because the output voltage at the CS pin can reach up to 130V. A fast switching diode with lower forward voltage and higher reverse voltage (150V), such as BAV20WS/BAS20W, can be used to enhance efficiency.

#### 5.3 Output Capacitor

Low-ESR capacitors should be used at the regulated boost output (CS pin) of the MIC4832 to minimize the switching output ripple voltage. The larger the output capacitance, the lower the output ripple at the CS pin. The reduced output ripple at the CS pin, along with a low-ESR capacitor, improves the efficiency of the MIC4832 circuit. Selection of the capacitor value will depend upon the peak inductor current, inductor size, and the load. The MIC4832 is designed for use with an output capacitance as low as 2.2 nF. For minimum audible noise, the use of a C0G/NPO dielectric output capacitor is recommended. TDK and AVX offer C0G/NPO dielectric capacitors in capacitances up to 2.7 nF at 200V to 250V rating in 0805 size. If output ripple is a concern, a 0.01 µF/200V X7R output capacitor is recommended.

## 5.4 EL Lamp Terminals (VA, VB)

An EL lamp is connected from VA to VB as the load. The high voltage alternated across VA and VB by the H-Bridge cycles generate luminance. The voltage at VA and VB should not exceed the voltage at V $_{CS}$  by more than 3V. This situation may become present when noisy enable signals such as those often generated by mechanical switches are applied to the driver's inputs. To prevent overvoltage at VA and VB, 10 k $\Omega$  resistors may be placed in series from VA to the EL panel and from VB to the EL panel. An alternative to the use of 10 k $\Omega$  resistors is to apply a diode from the CS pin to VA and VB, where the cathode of the diode is on the CS side and the anode is on the VA and VB side, respectively.

# 6.0 APPLICATION CIRCUIT

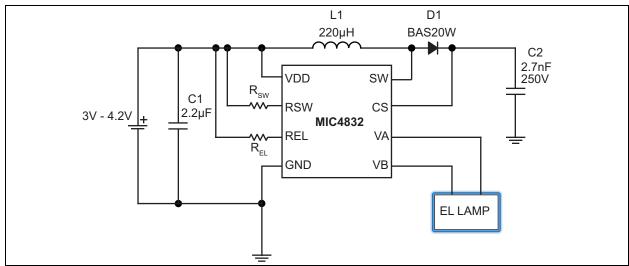


FIGURE 6-1: Typical Li-lon Powered MIC4832 Circuit.

TABLE 6-1: RECOMMENDED R<sub>SW</sub> & R<sub>EL</sub> VALUES FOR VARIOUS PANEL SIZES

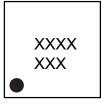
Size	Сар.	Lamp Freq.	100 Hz	200 Hz	300 Hz	400 Hz	500 Hz	600 Hz	700 Hz	800 Hz	900 Hz
_	_	R <sub>EL</sub>	2.82 MΩ	1.69 ΜΩ	1.1 ΜΩ	0.837 ΜΩ	0.665 ΜΩ	0.562 ΜΩ	0.471 ΜΩ	0.409 ΜΩ	0.369 ΜΩ
0.4 in <sup>2</sup>	2 nF	R <sub>SW</sub>	240 kΩ	252 kΩ	273 kΩ	281 kΩ	257 kΩ	269 kΩ	281 kΩ	_	_
0.4 111   2 115	f <sub>SW</sub>	150 kHz	143 kHz	132 kHz	128 kHz	116 kHz	105 kHz	98 kHz	_	_	
1 in <sup>2</sup>	4:-2 5-5	R <sub>SW</sub>	257 kΩ	295 kΩ	353 kΩ	_	_	_	_	_	_
1 in <sup>2</sup>   5 nF	f <sub>SW</sub>	140 kHz	122 kHz	102 kHz	_	_	_	_	_	_	
2 in <sup>2</sup>	2 in <sup>2</sup> 10 nF	R <sub>SW</sub>	300 kΩ	333 kΩ	_	_	_	_	_	_	_
2111   1011F	10 11	f <sub>SW</sub>	120 kHz	108 kHz	_	_	_	_	_	_	_
3 in <sup>2</sup> 15 nF	R <sub>SW</sub>	313 kΩ	_	_	_	_	_	_	_	_	
	19 115	f <sub>SW</sub>	115 kHz	_	_	_	_	_	_	_	_

Table 6-1 applies to the circuit shown in Figure 6-1.

#### 7.0 PACKAGING INFORMATION

## 7.1 Package Marking Information

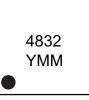
8-Lead MSOP\*



8-Lead DFN\*



Example



Example



**Legend:** XX...X Product code or customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

e3 Pb-free JEDEC® designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

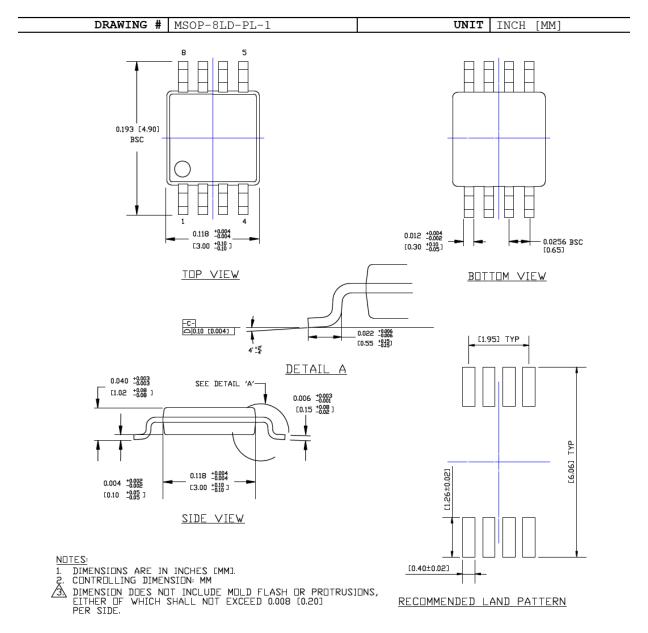
•, ▲, ▼ Pin one index is identified by a dot, delta up, or delta down (triangle mark).

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information. Package may or may not include the corporate logo.

Underbar (\_) and/or Overbar (¯) symbol may not be to scale.

#### TITLE

8 LEAD MSOP PACKAGE OUTLINE & RECOMMENDED LAND PATTERN

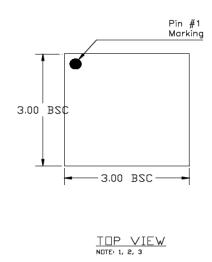


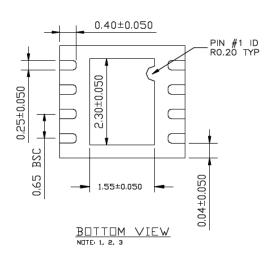
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging.

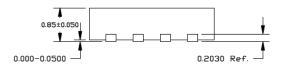
#### TITLE

8 LEAD DFN 3x3mm PACKAGE OUTLINE & RECOMMENDED LAND PATTERN

DRAWING # DFN33-8LD-PL-1 UNIT MM







SIDE VIEW

#### NOTE:

NOTE:

1. MAX PACKAGE WARPAGE IS 0.05 MM

2. MAX ALLOWABLE BURR IS 0.076MM IN ALL DIRECTIONS

3. PIN #1 IS ON TOP WILL BE LASER MARKED

4. RED CIRCLE IN LAND PATTERN INDICATE THERMAL VIA. SIZE SHOULD

0.30-0.35 MM IN DIAMETER AND SHOULD BE CONNECTED TO GND FOR MAX
THERMAL PERFORMANCE

5. CREEN PERFORMANCE

5. CREEN PERFORMANCE

6. CREEN PERFORMANCE SIZE SHOULD BE

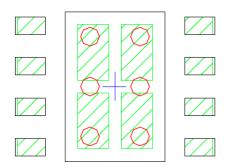
5. GREEN RECTANGLES (SHADED AREA) INDICATE SOLDER STENCIL OPENING ON EXPOSED PAD AREA. SIZE SHOULD BE 0.50×0.90 MM IN SIZE, 0.20 MM SPACING.

For the most current package drawings, please see the Microchip Packaging Specification located at Note: http://www.microchip.com/packaging.

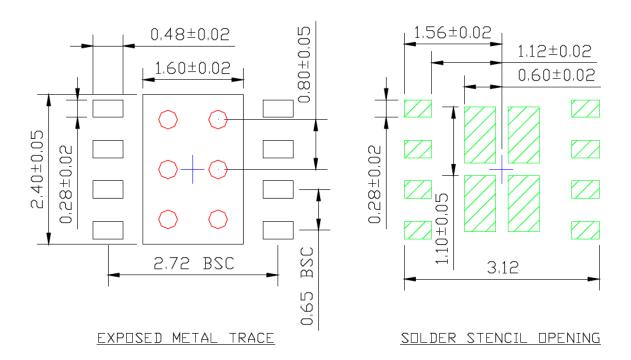
DS20006163A-page 14

# POD-Land Pattern drawing #DFN33-8LD-PL-1

# RECOMMENDED LAND PATTERN NOTE: 4, 5



STACKED-UP



Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging.

NOTES:

# APPENDIX A: REVISION HISTORY

# Revision A (March 2019)

- Converted Micrel document MIC4832 to Microchip data sheet template DS20006163A.
- Minor grammatical text changes throughout.

NOTES:

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

				Example	es:	
<b>Device</b> Part No.	<b>X</b> Junction Temp. Range	<u>XX</u> Package	- <u>XX</u> Media Type	a) MIC48	32YMM:	MIC4832, -40°C to +85°C Temperature Range, 8-Lead MSOP, 100/Tube
Device:	MIC4832: Lc	w Noise 220V <sub>PP</sub> EL	Driver	b) MIC48	32YMM-TR:	MIC4832, -40°C to +85°C Temperature Range, 8-Lead MSOP, 2,500/Reel
Junction Temperature Range:	Y = -40°C to	+85°C, Industrial		c) MIC48	32YML-TR:	MIC4832, -40°C to +85°C Temperature Range, 8-Lead 3 mm x 3 mm DFN, 5,000/Reel
Package:	MM = 8-Lead ML = 8-Lead 3	MSOP 3 mm x 3 mm DFN		Note 1:	catalog part nu	identifier only appears in the mber description. This identifier is
Media Type:		e (MM Package) eel (MM Package) eel (ML Package)			the device pac	ng purposes and is not printed on kage. Check with your Microchip r package availability with the option.

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